

Thyristor Module

tentative

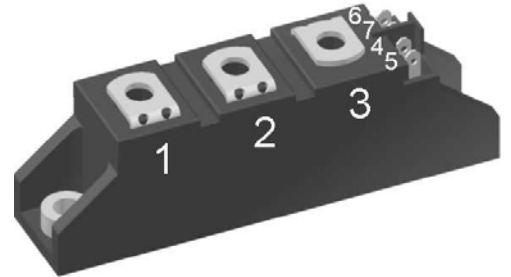
$$V_{RRM} = 2 \times 1600V$$

$$I_{TAV} = 110A$$

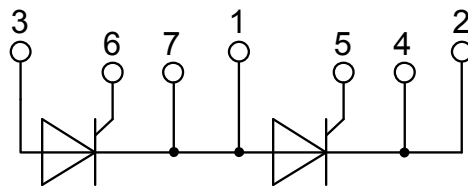
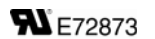
$$V_T = 1.21V$$

Phase leg

Part number

MCMA110P1600TA


Backside: isolated


Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

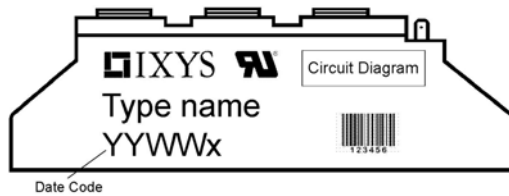
Package: TO-240AA

- Isolation Voltage: 4800V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1600	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		100	μA
		$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$		10	mA
V_T	forward voltage drop	$I_T = 110\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.24	V
		$I_T = 220\text{ A}$			1.52	V
		$I_T = 110\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		1.21	V
		$I_T = 220\text{ A}$			1.57	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$		110	A
$I_{T(RMS)}$	RMS forward current	180° sine			170	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$		0.85	V
r_T	slope resistance				3.3	m Ω
R_{thJC}	thermal resistance junction to case				0.3	K/W
R_{thCH}	thermal resistance case to heatsink			0.20		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		380	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		1.90	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		2.05	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$		1.62	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		1.75	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		18.1	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		17.5	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$		13.0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		12.7	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		95	pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$		10	W
		$t_p = 300\text{ }\mu\text{s}$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 330\text{ A}$			150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s};$ $I_G = 0.45\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 110\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}\text{C}$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$		1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		150	mA
			$T_{VJ} = -40^{\circ}\text{C}$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$				
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$		2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$				
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 110\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 140^{\circ}\text{C}$		185	μs

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Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{stg}	storage temperature		-40		125	°C	
T_{VJ}	virtual junction temperature		-40		140	°C	
Weight				90		g	
M_D	mounting torque		2.5		4	Nm	
M_T	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second	4800			V	
		t = 1 minute	4000			V	

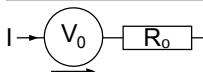

Part number

- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 110 = Current Rating [A]
- P = Phase leg
- 1600 = Reverse Voltage [V]
- TA = TO-240AA-1B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA110P1600TA	MCMA110P1600TA	Box	6	513383

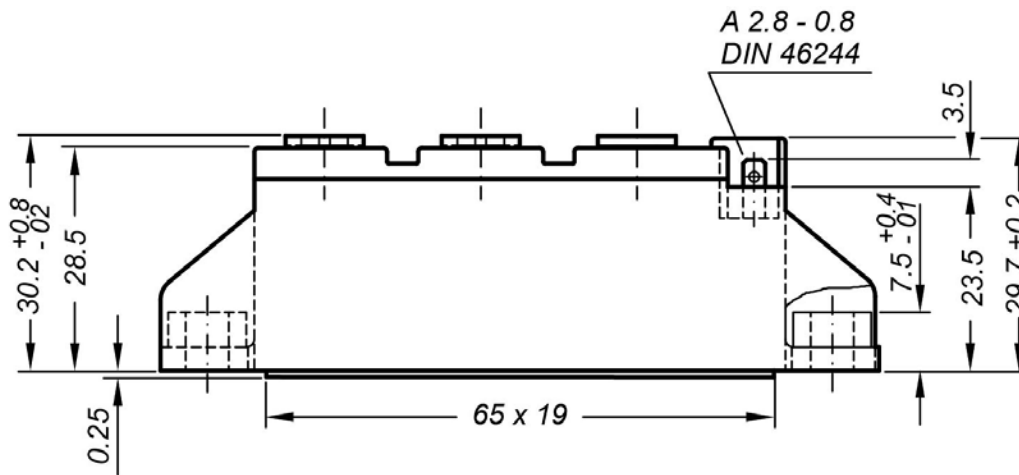
Equivalent Circuits for Simulation

* on die level

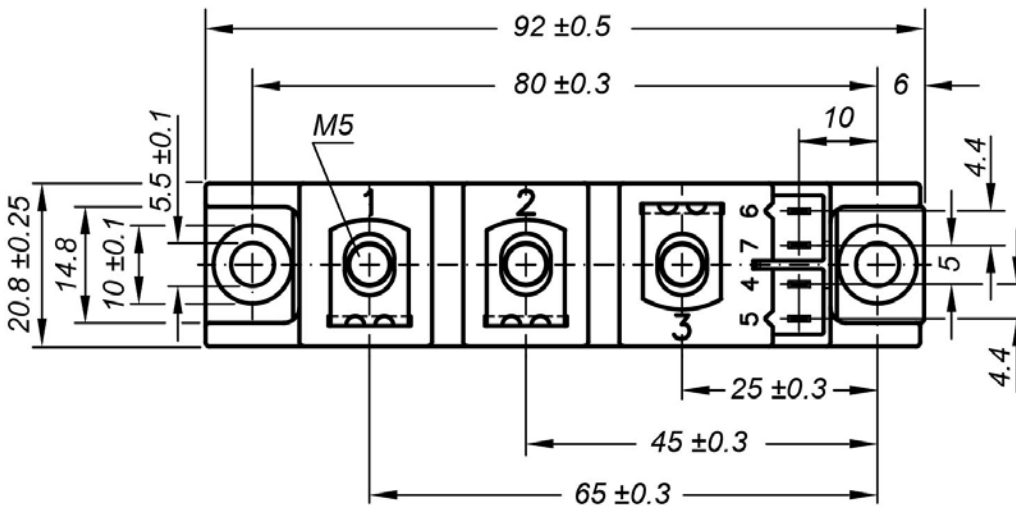
 $T_{VJ} = 140^{\circ}\text{C}$

Thyristor

$V_{0\max}$	threshold voltage	0.85	V
$R_{0\max}$	slope resistance *	2.1	mΩ

Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



Optional accessories: Keyed gate/cathode twin plugs
 Wire length: 350 mm, gate = white, cathode = red
 UL 758, style 3751
 Type ZY 200L (L = Left for pin pair 4/5)
 Type ZY 200R (R = Right for pin pair 6/7)

